

Description

The AU0542S2L is a 2-line bi-directional TVS diode array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AU0542S2L complies with the IEC 61000-4-2 (ESD) standard with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a 3-pin SOT-23 lead-free package. The small size and high ESD surge protection make AU0542S2L an ideal choice to protect cell phone, digital video interfaces, high speed data ports, and many other portable applications.

Features

- Ultra low leakage: nA level
- Operating voltage: 5V
- Low clamping voltage
- Small SOT-23 package
- Up to 2-line protects
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 6A (8/20 μs)
- RoHS Compliant

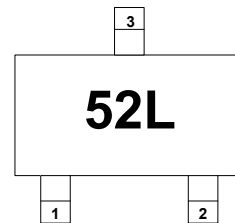
Mechanical Characteristics

- Package: SOT-23
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

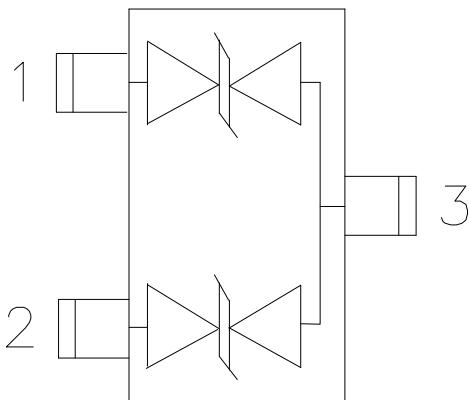
- Cellular Handsets and Accessories
- Notebooks and Handhelds
- Personal Digital Assistants
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players, Keypads, Side Keys, LCD
- USB 2.0

Marking Information



52L = Device Marking Code

Dimensions and Pin Configuration



Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
AU0542S2L	3000/Tape & Reel	7 inch

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

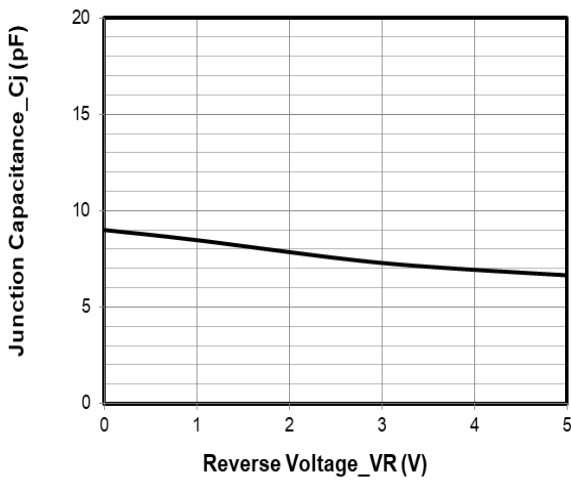
Parameter	Symbol	Value	Unit
ESD per IEC 61000-4-2 (Air)	VESD	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Peak Pulse Power (8/20 μs)	PPK	70	W
Peak Pulse Current	I _{PP}	6	A
Operating Temperature Range	T _J	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	T _{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

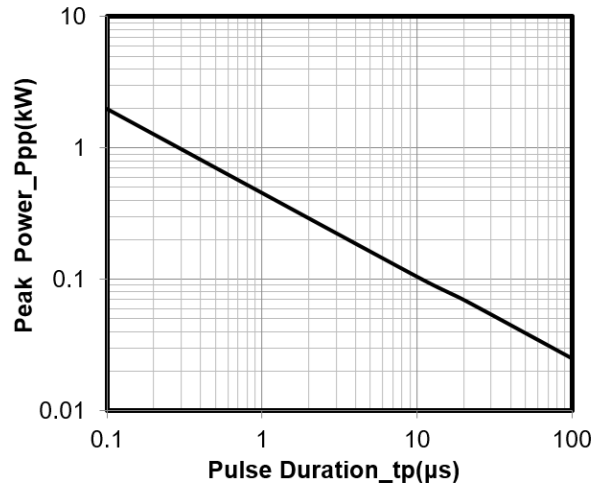
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			5	V	
Breakdown Voltage	V _{BR}	6			V	I _T = 1mA
Reverse Leakage Current	I _R			0.2	μA	V _{RWM} = 5V
Clamping Voltage	V _C			8	V	I _{PP} = 1A (8 x 20 μs pulse),
Clamping Voltage	V _C			11.7	V	I _{PP} = 6A (8 x 20 μs pulse)
Junction Capacitance	C _J		9		pF	V _R = 0V, f = 1MHz, any I/O pin to pin 3

Note 1: I/O pins are Pin 1, 2

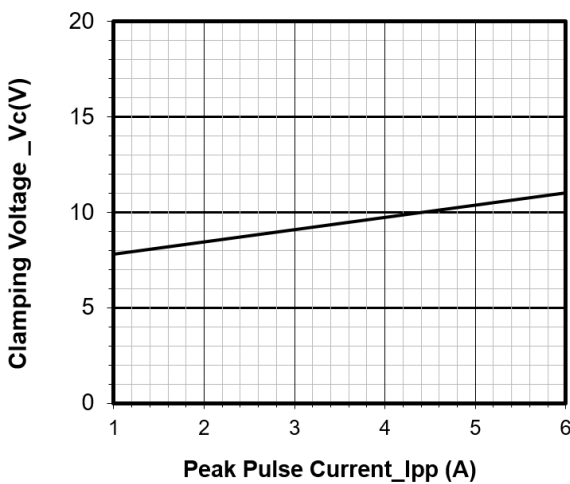
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



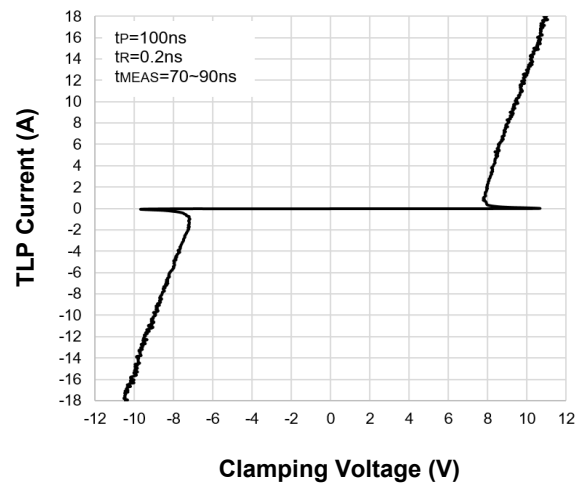
Junction Capacitance vs. Reverse Voltage



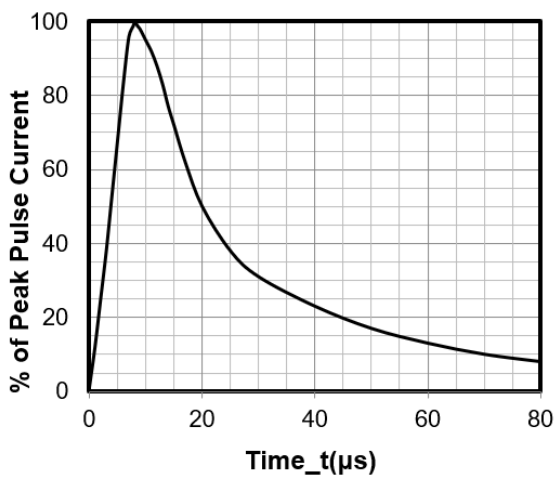
Peak Pulse Power vs. Pulse Time



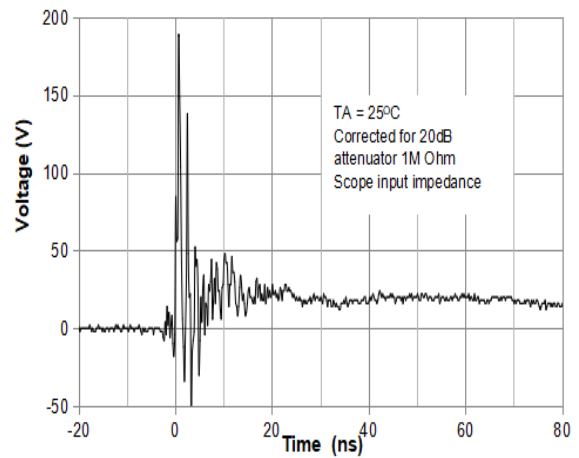
Clamping Voltage vs. Peak Pulse Current ($t_p = 8/20\mu\text{s}$)



TLP Curve

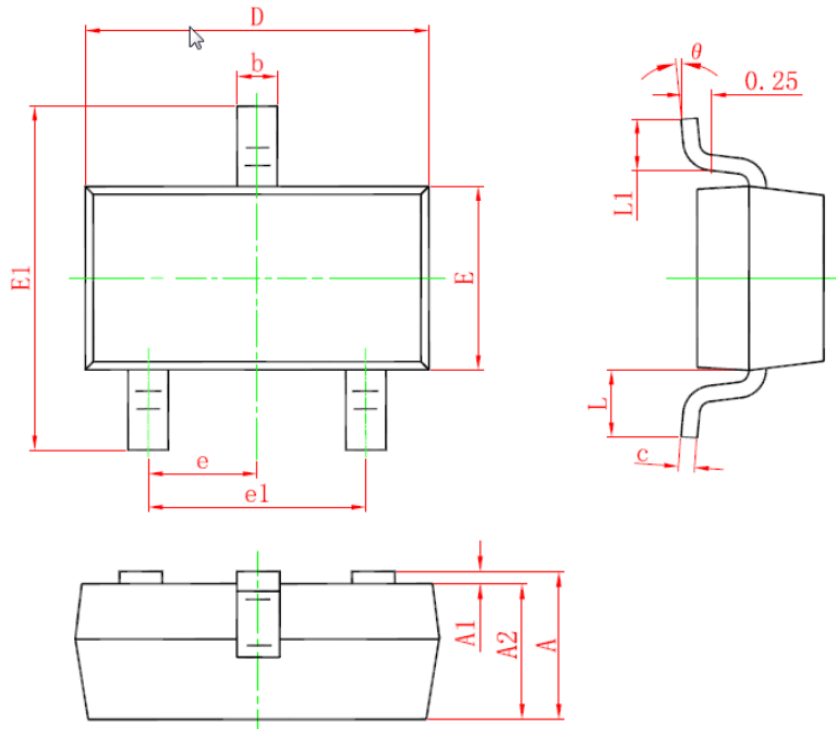


8 X 20μs Pulse Waveform



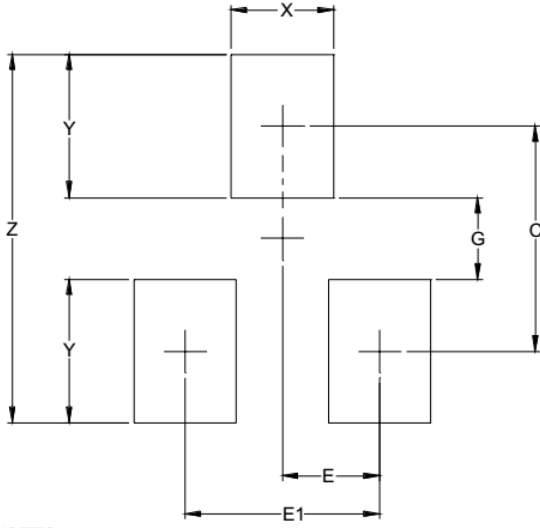
ESD Clamping Voltage

+8 kV Contact per IEC61000-4-2

SOT-23 Package Outline Drawing


SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	--	1.15	0.035	--	0.045
A1	0.00	--	0.10	0.000	--	0.004
A2	0.90	--	1.05	0.035	--	0.041
b	0.30	--	0.50	0.012	--	0.020
c	0.08	--	0.15	0.003	--	0.006
D	2.80	--	3.00	0.110	--	0.118
E	1.20	--	1.40	0.047	--	0.055
E1	2.25	--	2.55	0.089		0.100
e	0.95TYP			0.037TYP		
e1	1.80	--	2.00	0.071	--	0.079
L	0.55REF			0.022REF		
L1	0.30	--	0.50	0.012	--	0.020
θ	0°	--	8°	0°	--	8°

Suggested Land Pattern



SYM	DIMENSIONS	
	INCHES	MILLIMETERS
C	(.087)	(2.20)
E	.037	0.95
E1	.075	1.90
G	.031	0.80
X	.039	1.00
Y	.055	1.40
Z	.141	3.60

Contact Information

Applied Power Microelectronics Inc.

Website: <http://www.appliedpowermicro.com>

Email: sales@appliedpowermicro.com

Phone: +86 (0519) 8399 3606